

Three Phase Diode Bridge & Thyristor Module

V_{DRM} / **V**_{RRM} 800 to 1600V

I_{FAV}/I_{TAV} 200 Amp

Features

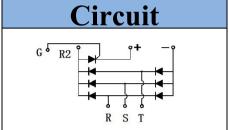
- Aluminum oxide DBC
- · Glass passivated chip

Applications

- Inverter for AC or DC motor control
- · Current stabilized power supply
- Switching power supply

Module Type





Туре	V _{RRM} / V _{DRM}	V_{RSM}
MDST200-08	800V	900V
MDST200-12	1200V	1300V
MDST200-16	1600V	1700V

Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Unit
I _D	Output Current	Three Phase, Full Wave T _c = 90°C	200	Α
I _{FSM}	Surge Forward Current	$T_j = 25$ °C, $t = 50$ Hz(10ms), $V_R = 0$ V	2240	Α
I ² t	Circuit Fusing Consideration	t = 10ms T _j =25°C	25088	A ² s
V _{ISO}	Isolation Breakdown Voltage	AC 50Hz/60Hz; R.M.S; 1min	3000	V
Tj	Operating Junction Temperature		-40 to +150	°C
T _{stg}	Storage Temperature		-40 to +125	°C
Mt		To Terminals(M4)	2±15%	
IVIt	Mounting Torque	To Terminals(M6) 5±15%		N⋅m
Ms		To Heatsink(M6)	5±15%	
Weight	Module (Approximately)		360	g

■ Thermal Characteristics

Symbol	Item	Conditions	Values	Unit
R _{th(j-c)}	Thermal Impedance, Max	Junction to Case(Per Module)	0.12	°C/W
R _{th(c-s)}	Thermal Impedance, Max	Case to Heat Sink	0.05	°C/W

Electrical Characteristics

Symbol	Item	Conditions	Values			Unit
Symbol	item	Conditions	Min.	Тур.	Max.	Ullit
V _{FM}	Forward Voltage Drop, Max	T _j = 25°C I _F = 200A	_	_	1.35	V
I _{RRM}	Repetitive Peak Reverse Current, Max	$T_j = 25$ °C $V_R = V_{RRM}$	_	_	0.5	mA
IRRM		$T_i = 150$ °C $V_R = V_{RRM}$	_	_	10	
V _{T0}	Threshold Voltage, for power loss calculation only	T _j = 125°C	0.80		V	
r _T	Slope Resistance, for power loss calculation only	T _j = 125°C	2.25		mΩ	

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Thyristor

■ Maximum Ratings

Symbol	Item	Conditions	Values	Unit
I _{TAV}	Average On-state Current	T _c = 90°C, Three Phase Full Wave Rectified	200	А
I _{TSM}	Surge On-state Current	$T_j = 25$ °C, $t = 50$ Hz(10ms), $V_R = 0$ V 2400		А
I ² t	Circuit Fusing Consideration		28800	A ² s
V _{ISO}	Isolation Breakdown Voltage	AC 50Hz; R.M.S;1min	3000	V
Tj	Operating Junction Temperature		-40 to + 125	°C
T _{stg}	Storage Temperature		-40 to + 125	°C
di/dt	Critical Rate of Rise of On-state Current, Max	T_j = 125°C, V_D = 1/2 V_{DRM} , I_G = 150mA, di_G/dt = 0.1A/ μ s	150	A/μs

■ Thermal Characteristics

Symbol	Item	Conditions	Values	Unit
R _{th(j-c)}	Thermal Impedance, Max	Junction to Case	0.14	°C/W
R _{th(c-s)}	Thermal Impedance, Max	Case to Heat Sink	0.05	°C/W

■ Electrical Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Тур.	Max.	Oilit
V _{TM}	Peak On-State Voltage, Max	$T_j = 25^{\circ}C$, $I_T = 200A$	-	-	1.30	V
I _{DRM} /I _{RRM}	Repetitive Peak Reverse Current, Max /Repetitive Peak Off-state Current, Max	$T_j = 125$ °C, $V_R = V_{RRM}$, $V_D = V_{DRM}$	-	-	30	mA
V _{GT}	Gate Trigger Voltage, Max	$T_j = 25^{\circ}C, V_D = 6V$	-	-	3.0	V
I _{GT}	Gate Trigger Current, Max	$T_j = 25^{\circ}C, V_D = 6V$	-	-	150	mA
V_{GD}	Gate Non-Trigger Voltage, Max	$T_j = 125$ °C, $V_D = 2/3V_{DRM}$	-	-	0.25	V
IL	Latching Current	T _j = 25°C	-	200	-	mA
I _H	Holding Current	T _j = 25°C	-	150	-	mA
t _{gt}	Turn On Time	T _j = 25°C	-	3	-	μs
dv/dt	Critical Rate of Rise of Off-state Voltage, Min	T _j = 125°C, V _D = 2/3V _{DRM} Linear Voltage Rise	500		V/µs	
V _{T0}	Threshold Voltage, for power loss calculation only	T _j = 125°C	0.89		V	
r _T	Slope Resistance, for power loss calculation only	T _j = 125°C	1.8		mΩ	

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Performance Curves

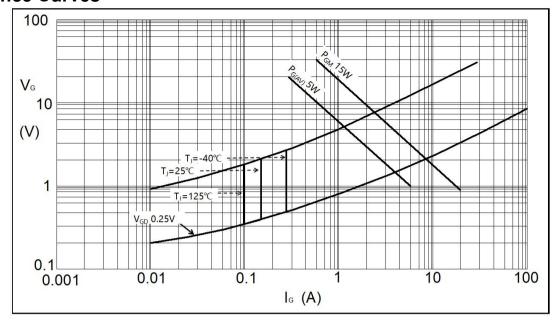
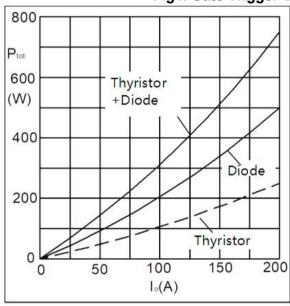


Fig1. Gate Trigger Characteristics



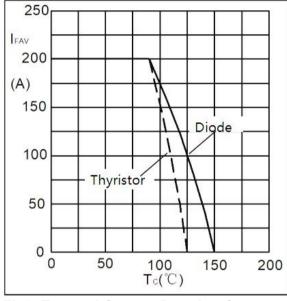


Fig2. Power Dissipation

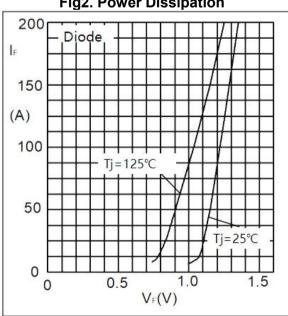


Fig3. Forward Current Derating Curve

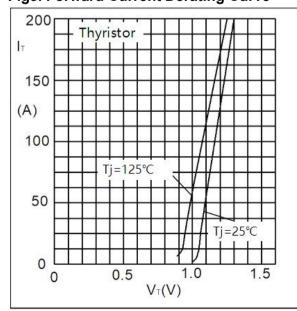


Fig4. Forward Characteristics



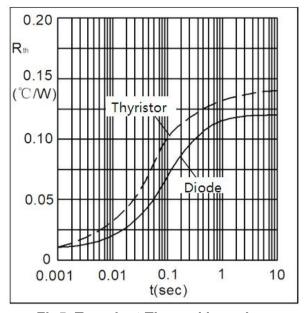


Fig5. Transient Thermal impedance

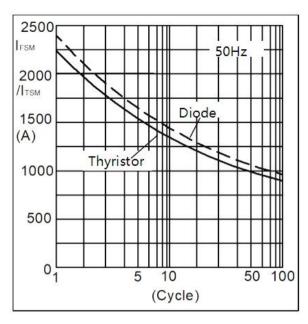
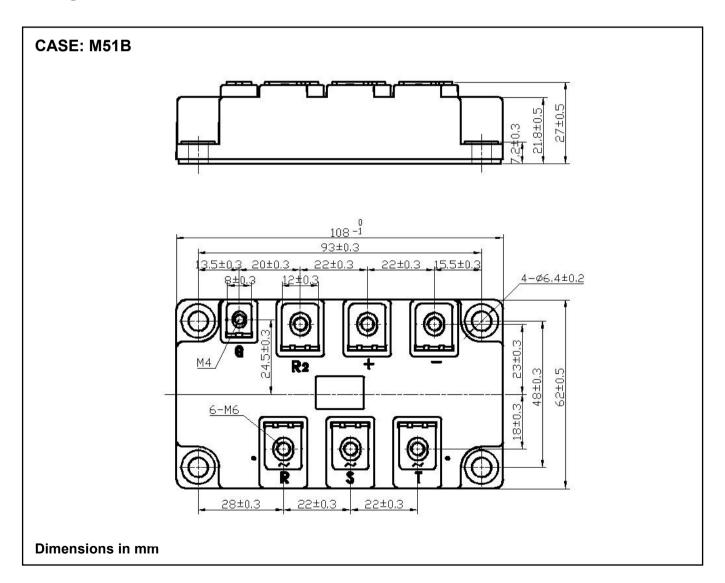


Fig6. Max Non-Repetitive Forward Surge Current

Package Outline Information





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